

PNP general purpose transistors

BC856; BC857; BC858

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

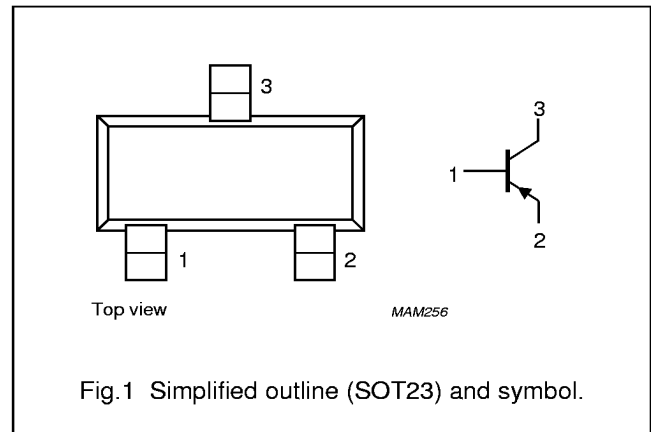
PNP transistor in a SOT23 plastic package.
NPN complements: BC846, BC847 and BC848.

MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BC856	3Dp	BC857C	3Gp
BC856A	3Ap	BC858	3Mp
BC856B	3Bp	BC858A	3Jp
BC857	3Hp	BC858B	3Kp
BC857A	3Ep	BC858C	3Lp
BC857B	3Fp		

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC856		–	–80	V
	BC857		–	–50	V
	BC858		–	–30	V
V_{CEO}	collector-emitter voltage	open base			
	BC856		–	–65	V
	BC857		–	–45	V
	BC858		–	–30	V
I_{CM}	peak collector current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	250	mW
h_{FE}	DC current gain	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}$	125	800	
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	MHz

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

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V _{CBO}	collector-base voltage	open emitter			
	BC856		–	–80	V
	BC857		–	–50	V
	BC858		–	–30	V
V _{CEO}	collector-emitter voltage	open base			
	BC856		–	–65	V
	BC857		–	–45	V
	BC858		–	–30	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–200	mA
I _{BM}	peak base current		–	–200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th-j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

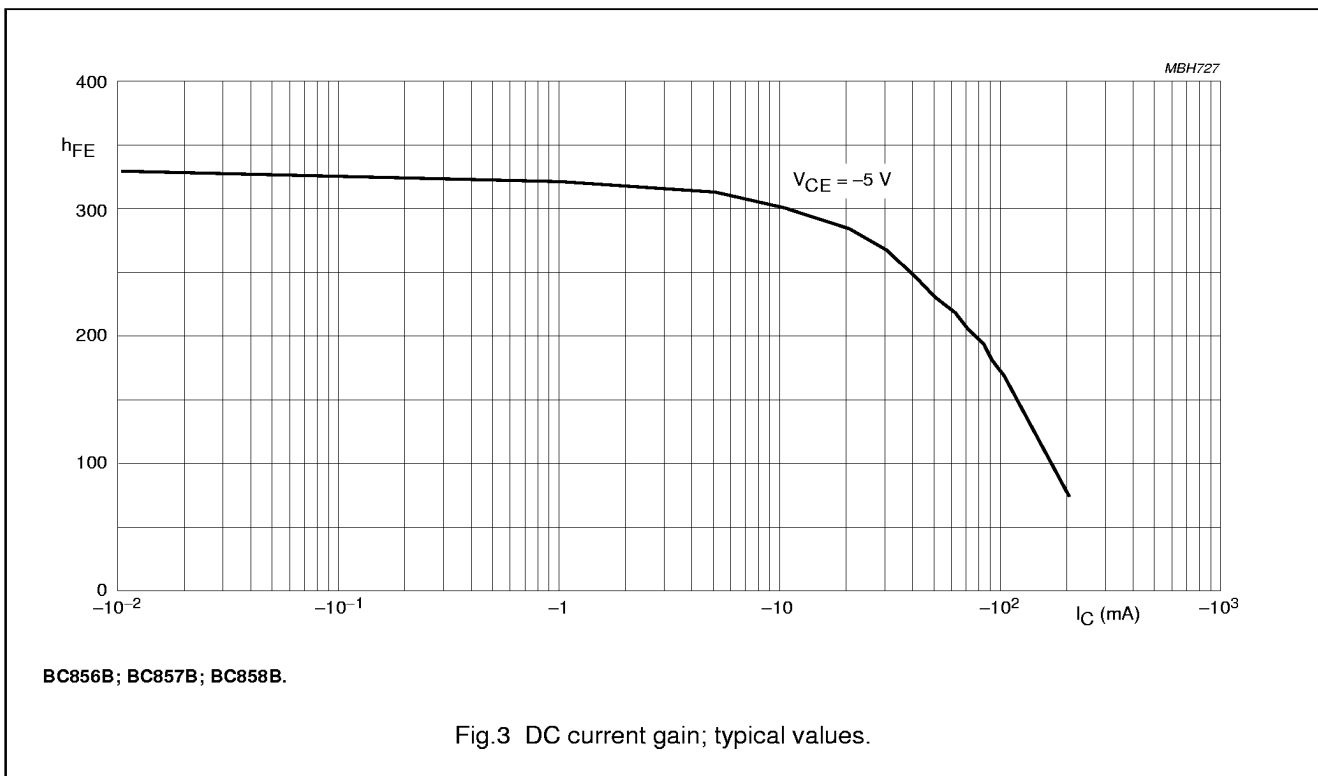
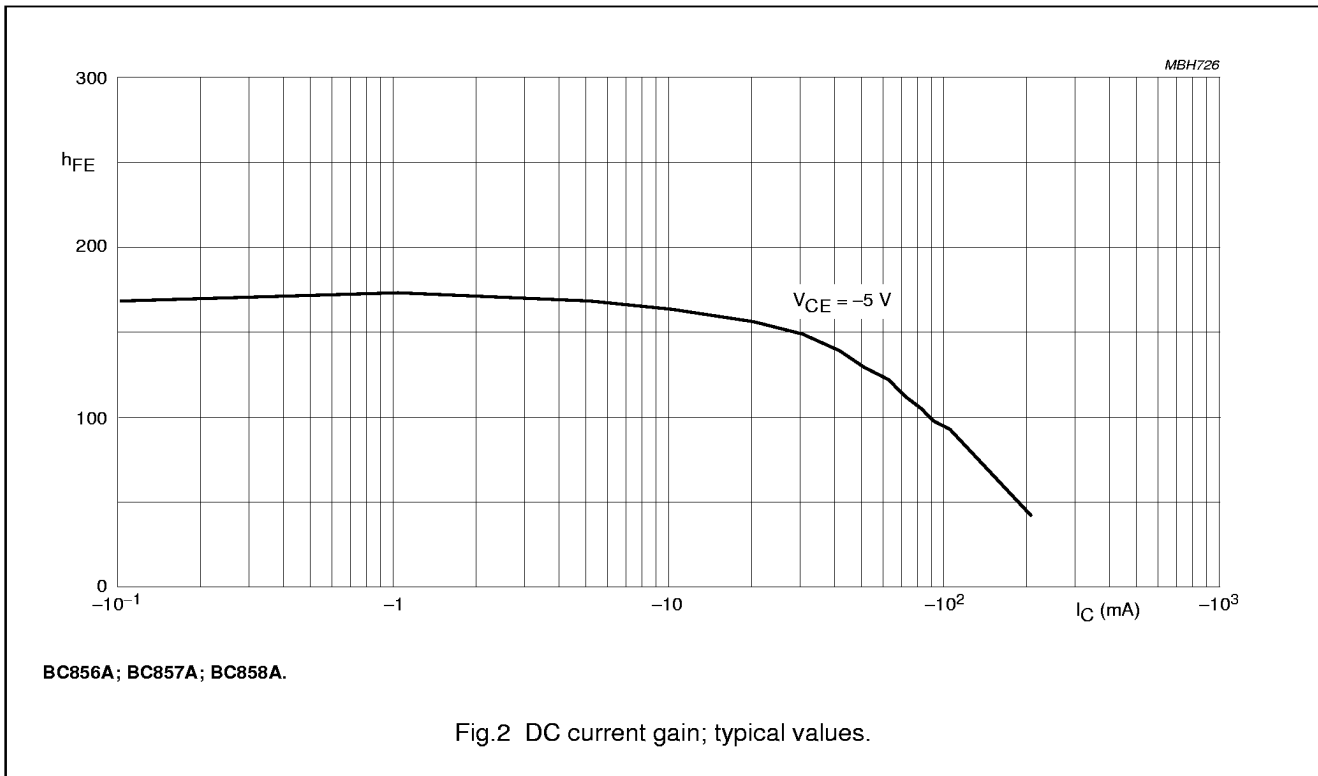
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–1	–15	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ °C}$	–	–	–4	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain BC856 BC857; BC858 BC856A; BC857A; BC858A BC856B; BC857B; BC858B BC857C; BC858C	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ see Figs 2, 3 and 4	125	–	475	
			125	–	800	
			125	–	250	
			220	–	475	
			420	–	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–75	–300	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA}$	–	–250	–650	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA};$ note 1	–	–700	–	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ note 1	–	–850	–	mV
V_{BE}	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–600	–650	–750	mV
		$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–	–	–820	mV
C_C	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	4.5	–	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	2	10	dB

Notes

- V_{BEsat} decreases by about -1.7 mV/K with increasing temperature.
- V_{BE} decreases by about -2 mV/K with increasing temperature.

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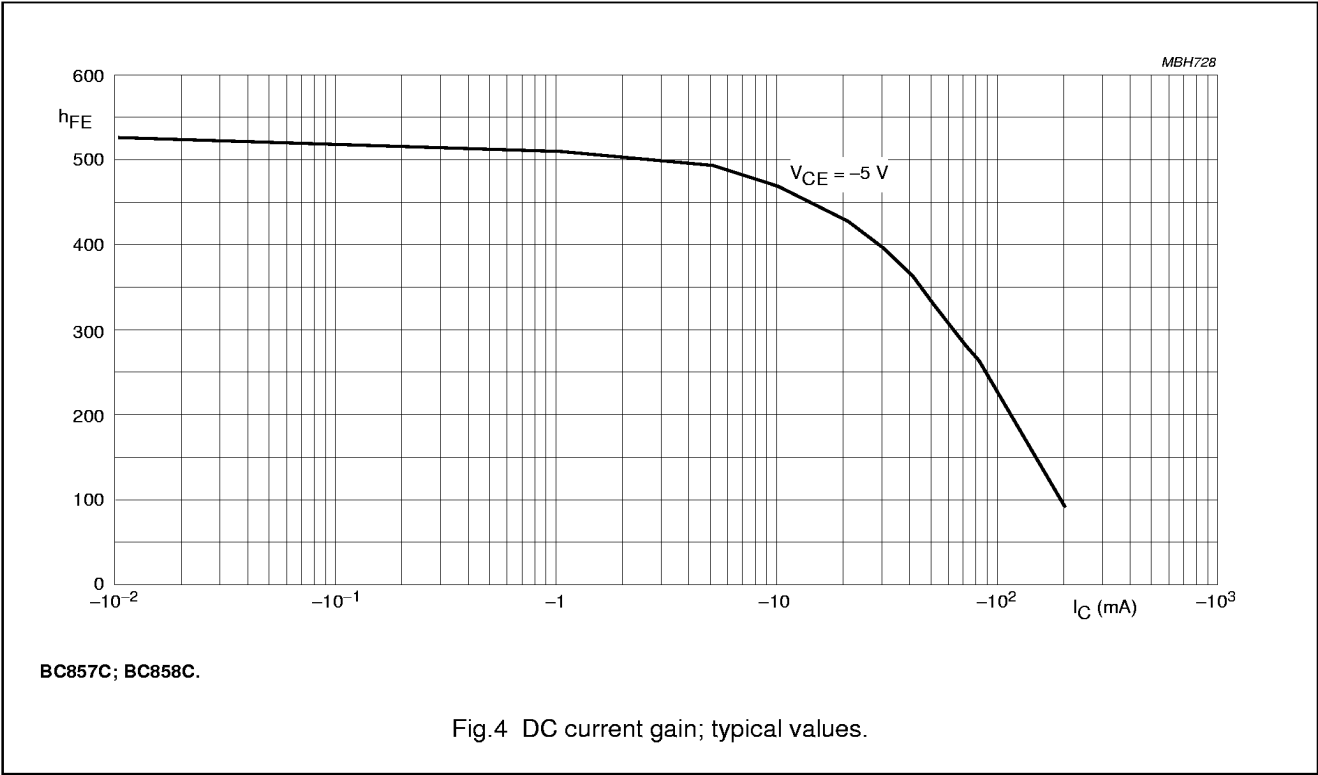


Fig.4 DC current gain; typical values.

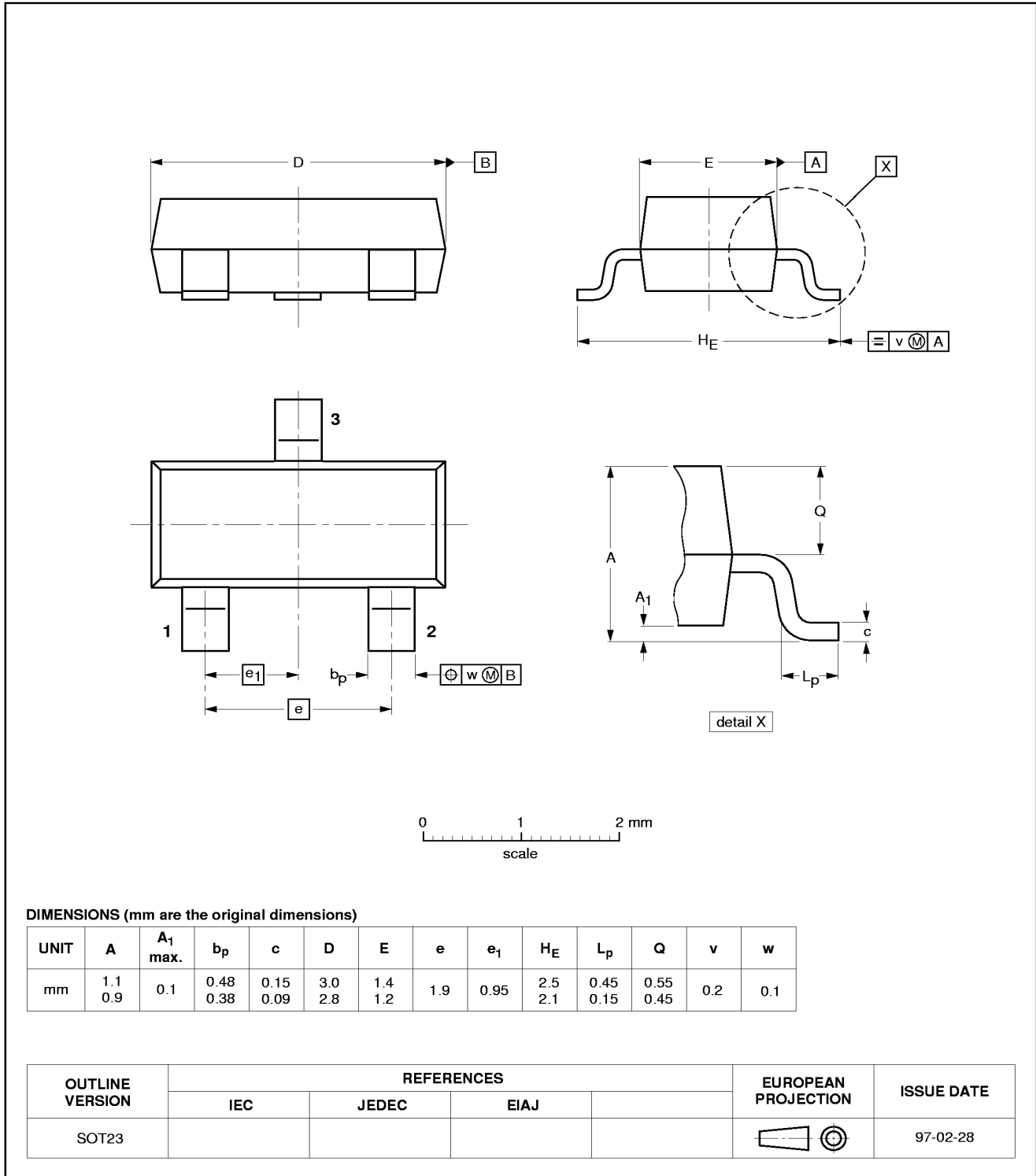
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



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